

tentative

High Voltage Standard Rectifier Module

$$V_{RRM} = 2 \times 2200 \text{ V}$$

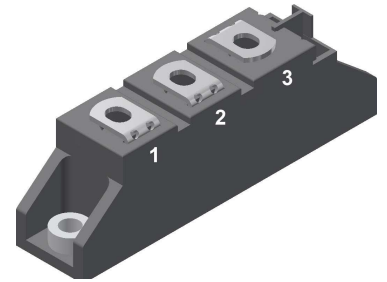
$$I_{FAV} = 85 \text{ A}$$

$$V_F = 1.1 \text{ V}$$

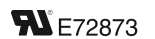
Phase leg

Part number

MDNA85P2200TG



Backside: isolated




Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

Applications:

- Diode for main rectification
- For single and three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Package: TO-240AA

- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Height: 30 mm
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

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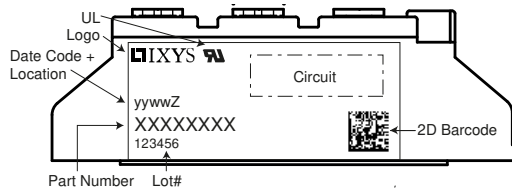


Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage					2300	V
V_{RRM}	max. repetitive reverse blocking voltage					2200	V
I_R	reverse current	$V_R = 2200$ V		$T_{VJ} = 25^\circ\text{C}$		100	μA
		$V_R = 2200$ V		$T_{VJ} = 150^\circ\text{C}$		2	mA
V_F	forward voltage drop	$I_F = 85$ A		$T_{VJ} = 25^\circ\text{C}$		1.15	V
		$I_F = 170$ A				1.38	V
		$I_F = 85$ A		$T_{VJ} = 125^\circ\text{C}$		1.10	V
		$I_F = 170$ A				1.39	V
I_{FAV}	average forward current	$T_C = 100^\circ\text{C}$		$T_{VJ} = 150^\circ\text{C}$		85	A
		rectangular	d = 0.5				
V_{FO}	threshold voltage			$T_{VJ} = 150^\circ\text{C}$		0.79	V
r_F	slope resistance					3.5	m Ω
		} for power loss calculation only					
R_{thJC}	thermal resistance junction to case					0.35	K/W
R_{thCH}	thermal resistance case to heatsink				0.2		K/W
P_{tot}	total power dissipation			$T_C = 25^\circ\text{C}$		350	W
I_{FSM}	max. forward surge current	t = 10 ms; (50 Hz), sine		$T_{VJ} = 45^\circ\text{C}$		1.50	kA
		t = 8,3 ms; (60 Hz), sine		$V_R = 0$ V		1.62	kA
		t = 10 ms; (50 Hz), sine		$T_{VJ} = 150^\circ\text{C}$		1.28	kA
		t = 8,3 ms; (60 Hz), sine		$V_R = 0$ V		1.38	kA
I^2t	value for fusing	t = 10 ms; (50 Hz), sine		$T_{VJ} = 45^\circ\text{C}$		11.3	kA ² s
		t = 8,3 ms; (60 Hz), sine		$V_R = 0$ V		10.9	kA ² s
		t = 10 ms; (50 Hz), sine		$T_{VJ} = 150^\circ\text{C}$		8.13	kA ² s
		t = 8,3 ms; (60 Hz), sine		$V_R = 0$ V		7.87	kA ² s
C_J	junction capacitance	$V_R = 400$ V; f = 1 MHz		$T_{VJ} = 25^\circ\text{C}$		60	pF



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Package TO-240AA		Ratings				
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			200	A
T_{VJ}	virtual junction temperature		-40		150	°C
T_{op}	operation temperature		-40		125	°C
T_{stg}	storage temperature		-40		125	°C
Weight				76		g
M_D	mounting torque		2.5		4	Nm
M_T	terminal torque		2.5		4	Nm
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	13.0	9.7		mm
$d_{Spb/Apb}$		terminal to backside	16.0	16.0		mm
V_{ISOL}	isolation voltage	t = 1 second	4800			V
		t = 1 minute	4000			V
		50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA				



Part description

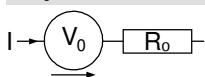
- M = Module
- D = Diode
- N = High Voltage Standard Rectifier
- A = ($\geq 2000V$)
- 85 = Current Rating [A]
- P = Phase leg
- 2200 = Reverse Voltage [V]
- TG = TO-240AA

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MDNA85P2200TG	MDNA85P2200TG	Box	36	

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 150^{\circ}C$

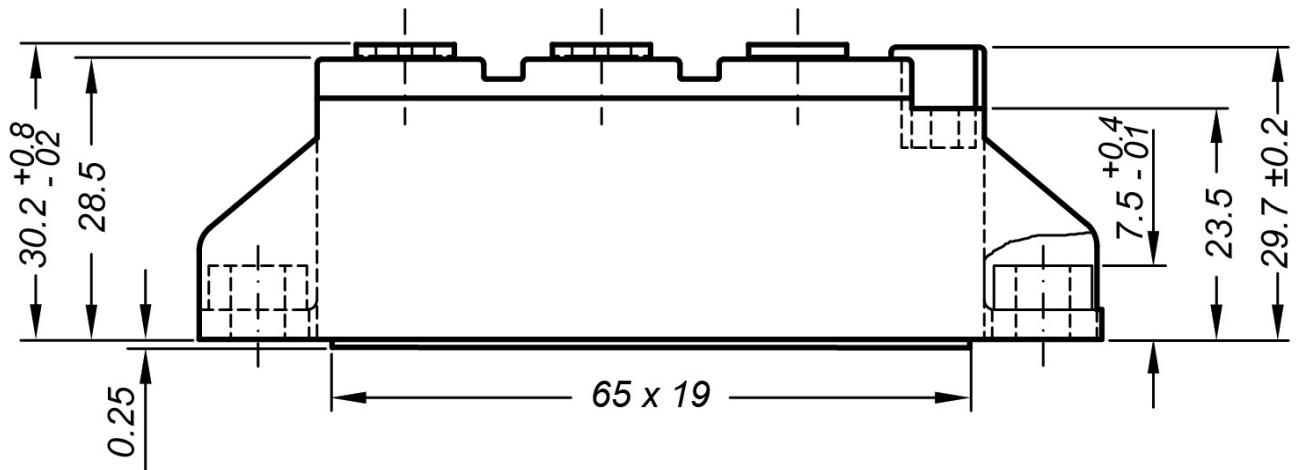


Rectifier

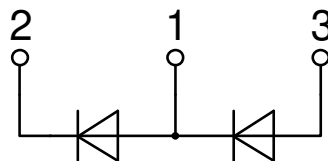
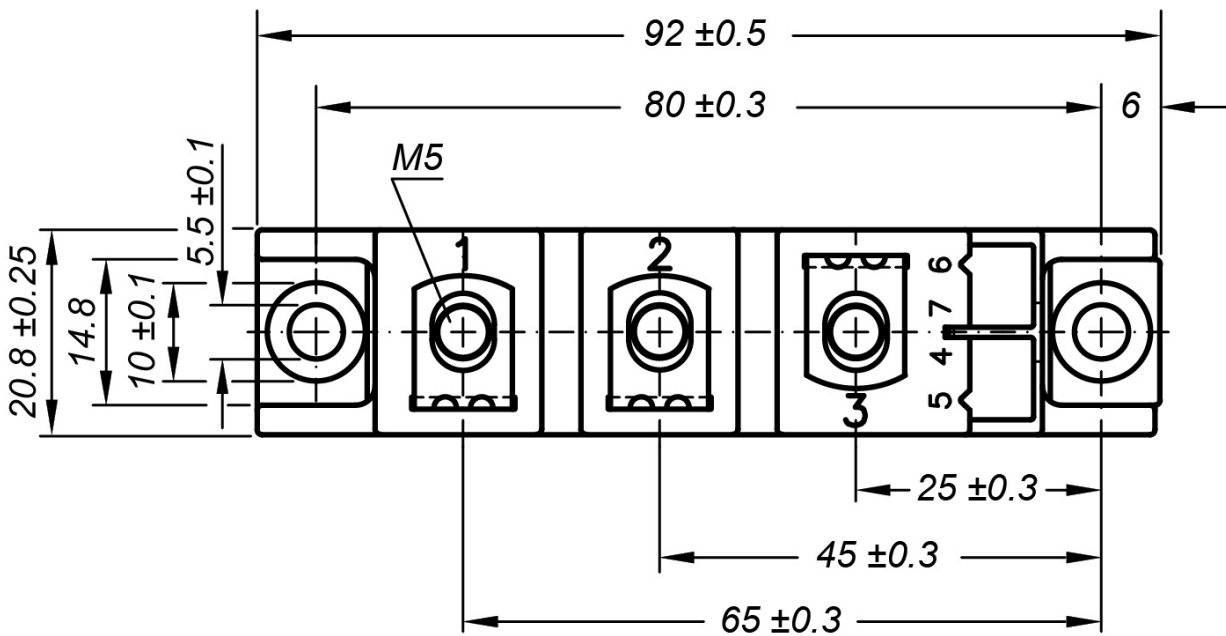
$V_{0\ max}$	threshold voltage	0.79	V
$R_{0\ max}$	slope resistance *	2.3	mΩ



Outlines TO-240AA



General tolerance: DIN ISO 2768 class „c“



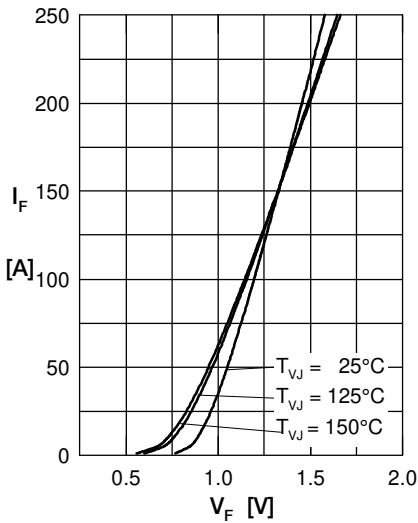
Rectifier


Fig. 1 Forward current versus voltage drop per diode

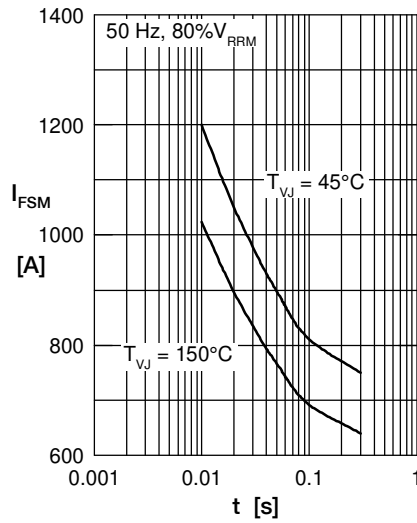


Fig. 2 Surge overload current vs. time per diode

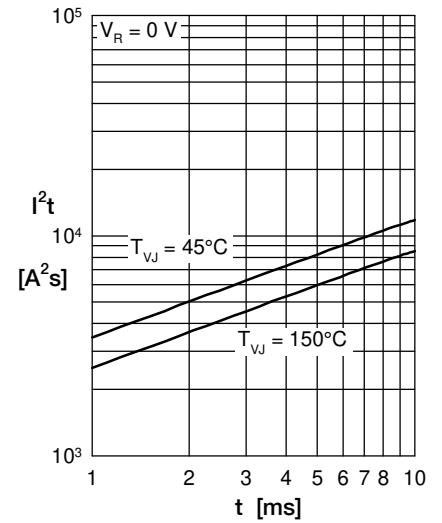
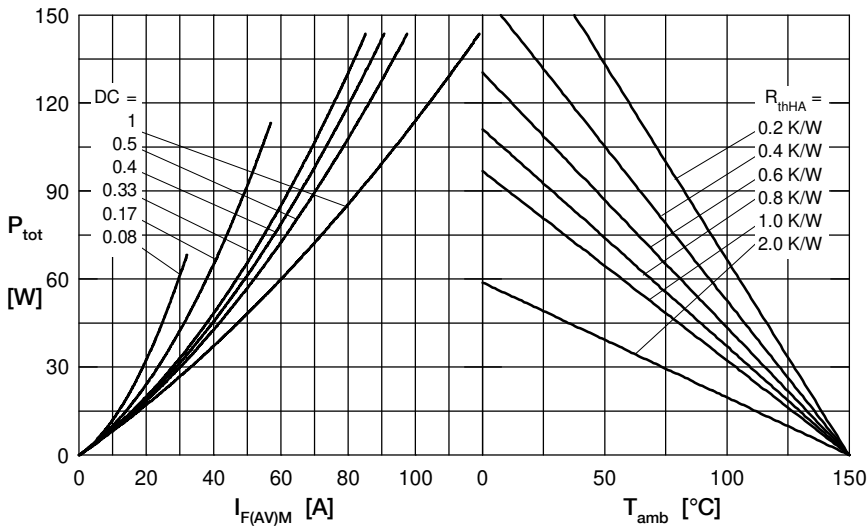

 Fig. 3 I^2t versus time per diode


Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

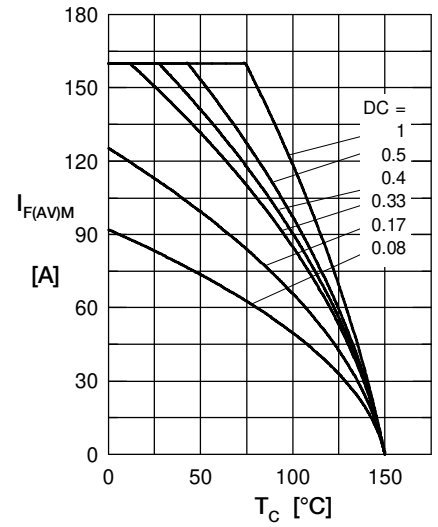


Fig. 5 Max. forward current vs. case temperature per diode

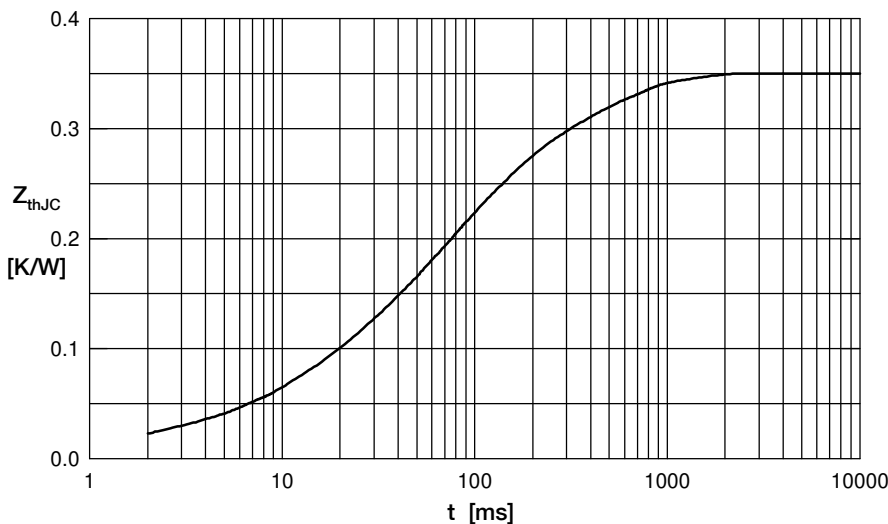


Fig. 6 Transient thermal impedance junction to case vs. time per diode

 Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.012	0.001
2	0.048	0.013
3	0.185	0.070
4	0.105	0.400